

# **Isc N-Channel MOSFET Transistor**

# STP30NF10FP

#### FEATURES

- Typical R<sub>DS</sub>(on)=0.038  $\Omega$
- · Application oriented characterization
- · Easy to drive
- 100% avalanche tested
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation





- High-efficiency DC-DC coverters
- Motor control

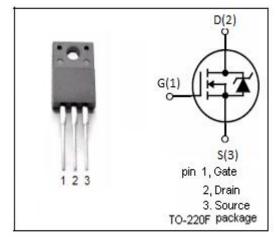


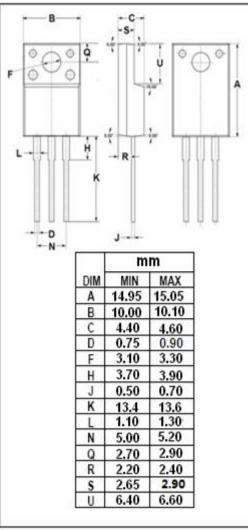
## • ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25℃)

| SYMBOL           | PARAMETER                                  | VALUE    | UNIT          |  |
|------------------|--|----------|---------------|--|
| V <sub>DSS</sub> | Drain-Source Voltage                       | 100      | V             |  |
| V <sub>GSS</sub> | Gate-Source Voltage                        | ±20      | V             |  |
| I <sub>D</sub>   | Drain Current-Continuous@Tc=25℃<br>Tc=100℃ | 18<br>13 | А             |  |
| I <sub>DM</sub>  | Drain Current-Single Pulsed                | 72       | А             |  |
| $P_D$            | Total Dissipation                          | 30       | W             |  |
| T <sub>j</sub>   | Operating Junction Temperature             | -55~175  | $^{\circ}$    |  |
| T <sub>stg</sub> | Storage Temperature                        | -55~175  | ${\mathbb C}$ |  |

### • THERMAL CHARACTERISTICS

| SYMBOL    | PARAMETER                                   |   | UNIT |  |
|-----------|---|---|------|--|
| Rth(ch-c) | Channel-to-case thermal resistance          | 5 | °C/W |  |
| Rth(ch-a) | ch-a) Channel-to-ambient thermal resistance |   | °C/W |  |







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### **ELECTRICAL CHARACTERISTICS**

T<sub>c</sub>=25℃ unless otherwise specified

| SYMBOL              | PARAMETER                      | CONDITIONS  | MIN | ТҮР | MAX     | UNIT |
|---------------------|--------------------------------|---|-----|-----|---------|------|
| BV <sub>DSS</sub>   | Drain-Source Breakdown Voltage | V <sub>GS</sub> =0V; I <sub>D</sub> = 0.25mA  | 100 |     |         | V    |
| V <sub>GS(th)</sub> | Gate Threshold Voltage         | V <sub>DS</sub> =±20V; I <sub>D</sub> =0.25mA   | 2   |     | 4       | V    |
| R <sub>DS(on)</sub> | Drain-Source On-Resistance     | V <sub>GS</sub> = 10V; I <sub>D</sub> =15A  |     | 38  | 45      | mΩ   |
| I <sub>GSS</sub>    | Gate-Source Leakage Current    | V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0V   |     |     | ±0.1    | μА   |
| I <sub>DSS</sub>    | Drain-Source Leakage Current   | V <sub>DS</sub> = 100V; V <sub>GS</sub> = 0V; T <sub>J</sub> =25°C<br>T <sub>J</sub> =125°C |     |     | 1<br>10 | μА   |
| V <sub>SDF</sub>    | Diode forward voltage          | I <sub>SD</sub> =30A, V <sub>GS</sub> = 0 V   |     |     | 1.3     | V    |

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2